



N-Channel 150 V (D-S) 175 °C MOSFET

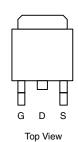
PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)	
150	0.073 at V _{GS} = 10 V	23	
	0.077 at V _{GS} = 6 V	22.5	

FEATURES

- TrenchFET[®] Power MOSFETS
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- **PWM Optimized**
- Compliant to RoHS Directive 2002/95/EC



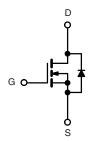
TO-263



Ordering Information: SUM23N15-73-E3 (Lead (Pb) free)

APPLICATIONS

· Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	GS ($T_C = 25$ °C, unless oth	erwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	150	V		
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	I-	23		
Continuous Diam Current (1) = 175 C)	T _C = 125 °C	I _D	13.4		
Pulsed Drain Current	I _{DM}	35	Α		
Avalanche Current	I _{AR}	25			
Repetitive Avalanche Energy ^a	L = 0.1 mH	E _{AR}	31	mJ	
	T _C = 25 °C	В	100 ^b	W	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	P _D	3.75		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.5		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).

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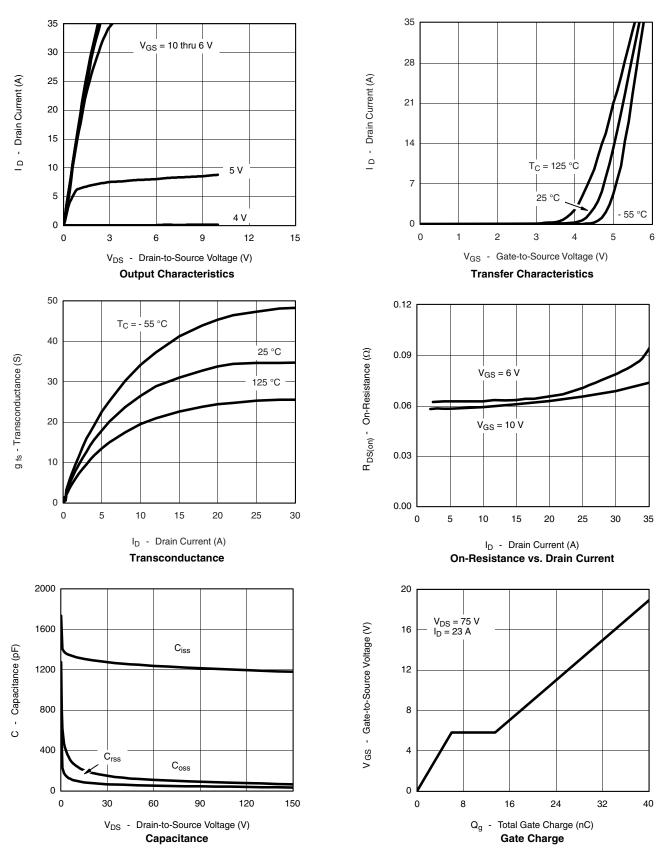
SPECIFICATIONS $(T_J = 25)$	°C, unless o	otherwise noted)				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150			- v
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	35			Α
		V _{GS} = 10 V, I _D = 15 A		0.059	0.073	
	D	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.140	1
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.168	Ω
		V _{GS} = 6 V, I _D = 10 A		0.062	0.077	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 25 A	10			S
Dynamic ^b	•			*		
Input Capacitance	C _{iss}			1290		pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		160		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ^c	Qg			22	35	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 23 \text{ A}$		6		
Gate-Drain Charge ^c	Q_{gd}			7.5		
Gate Resistance	R_{G}			4		Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 75 \text{ V}, R_L = 3.26 \Omega$ $I_D \cong 23 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		10	15	ns ns
Rise Time ^c	t _r			60	90	
Turn-Off Delay Time ^c	t _{d(off)}			30	43	
Fall Time ^c	t _f			45	70	
Source-Drain Diode Ratings and Cha	racteristics (7	_C = 25 °C) ^b				
Continuous Current	I _S				35	А
Pulsed Current	I _{SM}				23	
Forward Voltage ^a	V _{SD}	I _F = 23 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}			100	150	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 23 A, dl/dt = 100 A/μs		5	8	Α
Reverse Recovery Charge	Q _{rr}			0.25	0.6	μС

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



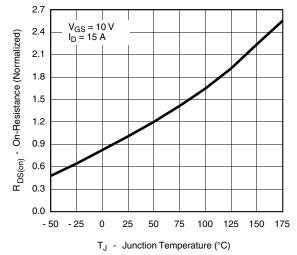
TYPICAL CHARACTERISTICS (25 °C unless noted)



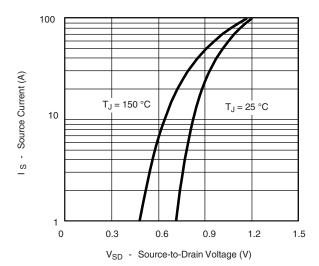
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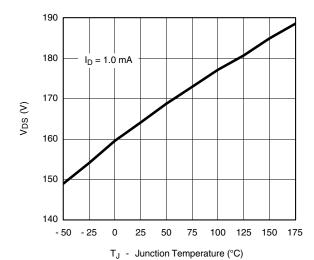
TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature



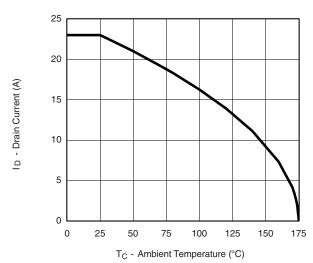
Source-Drain Diode Forward Voltage



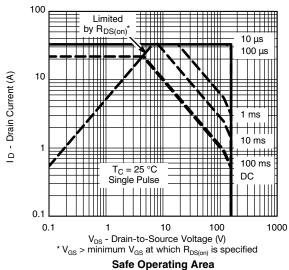
Drain Source Breakdown vs. Junction Temperature

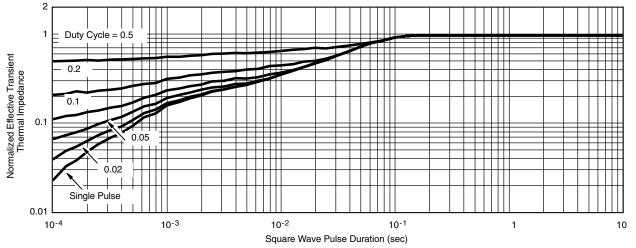


THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature





Normalized Thermal Transient Impedance, Junction-to-Case

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